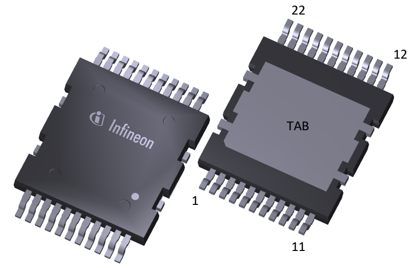
MOSFET

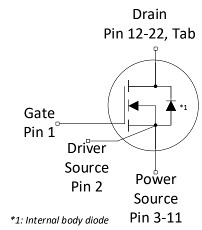
600V CoolMOS™ SJ S7 Power Device

IPDQ60R010S7 enables the best price performance for low frequency switching applications. CoolMOS™ S7 boasts the lowest $R_{DS(on)}$ values for a HV SJ MOSFET, with distinctive increase of energy efficiency.

CoolMOS™ S7 is optimized for "static switching" and high current applications. It is an ideal fit for solid state relay and circuit breaker designs as well as for line rectification in SMPS and inverter topologies.

PG-HDSOP-22





Features

- CoolMOS™ S7 technology enables 10mΩ $R_{DS(on)}$ in the smallest footprint
- Optimized price performance in low frequency switching applications
- High pulse current capability
- Kelvin Source pin improves switching performance at high current
- QDPAK (PG-HDSOP-22-1) offers top side cooling with improved package thermals

Benefits

- Minimized conduction losses (eliminate / reduce heat sink)
- Increased system performance
- More compact and easier design
- Lower BOM or/and TCO over prolonged life time

Compared to electromechanical devices:
- Faster switching times
- Higher reliability and longer system life time
- Shock & vibration resistance
- No contact arcing, bouncing or degradation over life time

Potential applications

- Solid state relays and circuit breakers
- Line rectification in high power/performance applications e.g. Computing, Telecom, UPS and Solar

Product validation

Fully qualified according to JEDEC for Industrial Applications

Please note: The source and sense source pins are not exchangeable. Their exchange might lead to malfunction. For paralleling 4pin MOSFET devices the placement of the gate resistor is generally recommended to be on the Driver Source instead of the Gate.

Table 1 Key Performance Parameters

Parameter	Value	Unit
$R_{DS(on),max}$	10	mΩ
$Q_{g,typ}$	318	nC
V_{SD}	0.82	V
Pulsed I_{SD}, I_{DS}	801	A

Type / Ordering Code	Package	Marking	Related Links
IPQC60R010S7	PG-HDSOP-22	60R010S7	see Appendix A

Table of Contents

1 Maximum ratings

at T_j = 25°C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain current rating	I_D	-	-	50	A	T_C=140°C Current is limited by $T_{j\,max}$ = 150°C; Lower case temp does increase current capability
Pulsed drain current[1]	$I_{D,pulse}$	-	-	801	A	T_C=25°C
High current turn off[2]	$I_{D,turn\ off}$	-	-	180	A	Current is limited by $T_{j\,max}$ = 150°C
Avalanche energy, single pulse	E_{AS}	-	-	616	mJ	I_D=6.3A; V_{DD}=50V; see table 10
Avalanche current, single pulse	I_{AS}	-	-	6.3	A	-
MOSFET dv/dt ruggedness[3]	dv/dt	-	-	20	V/ns	V_{DS}= 0V to 300V
Gate source voltage (static)	V_{GS}	-20	-	20	V	static
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC (f>1 Hz)
Power dissipation	P_{tot}	-	-	694	W	T_C=25°C
Storage temperature	T_{stg}	-55	-	150	°C	-
Operating junction temperature	T_j	-55	-	150	°C	-
Mounting torque	-	-	-	n.a.	Ncm	-
Diode forward current rating	I_S	-	-	50	A	T_C=140°C Current is limited by $T_{j\,max}$ = 150°C; Lower case temp does increase current capability
Diode pulse current[1]	$I_{S,pulse}$	-	-	801	A	T_C=25°C
Reverse diode dv/dt[4]	dv/dt	-	-	5	V/ns	V_{DS}=0 to 300V, I_{SD}<=50A, T_j=25°C see table 8
Maximum diode commutation speed	di_f/dt	-	-	1000	A/µs	V_{DS}=0 to 300V, I_{SD}<=50A, T_j=25°C see table 8
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	V_{rms}, T_C=25°C, t=1min

[1] Pulse width t_p limited by $T_{j,max}$
[2] A high current turn-off in SSR (solid state relays), SSCB (solid state circuit breaker) and motor starter applications must be limited to a maximum of 180A, as measurements have shown device destruction above this limit. This behavior is typically only limiting the usage of the mentioned applications. For any kind of server, telecom, industrial... applications, this high current turn-off represents a very unusual operation which is assumed not to take place at all. A possible solution is to use an additional current sense in order to have redundant current protection. Customer has to ensure that the turn-off current in the application is not exceeding 180A.
[3] The dv/dt has to be limited by appropriate gate resistor
[4] Identical low side and high side switch

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.18	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	device on PCB, minimal footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	45	55	°C/W	Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thickness) copper area. Tap exposed to air. PCB is vertical without air stream cooling.
Soldering temperature, reflow soldering allowed	T_{sold}	-	-	260	°C	reflow MSL1

3 Electrical characteristics

at T_j=25°C, unless otherwise specified

Table 4 Static characteristics

For any questions in this regard, please contact Infineon sales office.
For applications with applied blocking voltage >70% of the specified blocking voltage, it is required that the customer evaluates the impact of cosmic radiation effect in early design phase and contacts the Infineon sales office for the necessary technical support by Infineon

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	-	-	V	V_{GS}=0V, I_D=1mA
Gate threshold voltage	$V_{(GS)th}$	3.5	4.0	4.5	V	V_{DS}=V_{GS}, I_D=3.08mA
Zero gate voltage drain current	I_{DSS}	- -	- 80	8 -	µA	V_{DS}=600V, V_{GS}=0V, T_j=25°C V_{DS}=600V, V_{GS}=0V, T_j=150°C
Gate-source leakage current	I_{GSS}	-	-	100	nA	V_{GS}=20V, V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	- -	0.009 0.022	0.010 -	Ω	V_{GS}=12V, I_D=50A, T_j=25°C V_{GS}=12V, I_D=50A, T_j=150°C
Gate resistance	R_G	-	0.45	-	Ω	f=1MHz, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	11986	-	pF	V_{GS}=0V, V_{DS}=300V, f=250kHz
Output capacitance	C_{oss}	-	187	-	pF	V_{GS}=0V, V_{DS}=300V, f=250kHz
Effective output capacitance, energy related[1]	$C_{o(er)}$	-	644	-	pF	V_{GS}=0V, V_{DS}=0 to 300V
Effective output capacitance, time related[2]	$C_{o(tr)}$	-	5716	-	pF	I_D=constant, V_{GS}=0V, V_{DS}=0 to 300V
Output charge	Q_{oss}	-	50	-	nC	V_{GS}=0V, V_{DS}=0 to 300V
Turn-on delay time	$t_{d(on)}$	-	50	-	ns	V_{DD}=300V, V_{GS}=13V, I_D=50A, R_G=3Ω; see table 9
Rise time	t_r	-	5	-	ns	V_{DD}=300V, V_{GS}=13V, I_D=50A, R_G=3Ω; see table 9
Turn-off delay time	$t_{d(off)}$	-	180	-	ns	V_{DD}=300V, V_{GS}=13V, I_D=50A, R_G=3Ω; see table 9
Fall time	t_f	-	9	-	ns	V_{DD}=300V, V_{GS}=13V, I_D=50A, R_G=3Ω; see table 9

[1] $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 300V
[2] $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 300V

Table 6 Gate charge characteristics

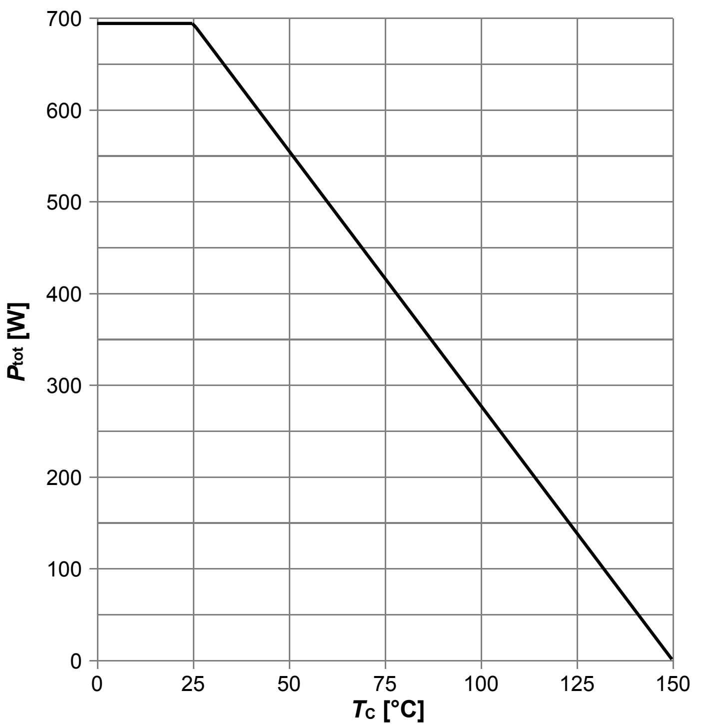
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	65	-	nC	V_{DD}=300V, I_D=50A, V_{GS}=0 to 12V
Gate to drain charge	Q_{gd}	-	106	-	nC	V_{DD}=300V, I_D=50A, V_{GS}=0 to 12V
Gate charge total	Q_g	-	318	-	nC	V_{DD}=300V, I_D=50A, V_{GS}=0 to 12V
Gate plateau voltage	$V_{plateau}$	-	5.4	-	V	V_{DD}=300V, I_D=50A, V_{GS}=0 to 12V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.82	-	V	V_{GS}=0V, I_F=50A, T_j=25°C
Reverse recovery time	t_{rr}	-	600	-	ns	V_R=300V, I_F=50A, di_F/dt=100A/µs; see table 8
Reverse recovery charge	Q_{rr}	-	17	-	µC	V_R=300V, I_F=50A, di_F/dt=100A/µs; see table 8
Peak reverse recovery current	I_{rrm}	-	55	-	A	V_R=300V, I_F=50A, di_F/dt=100A/µs; see table 8

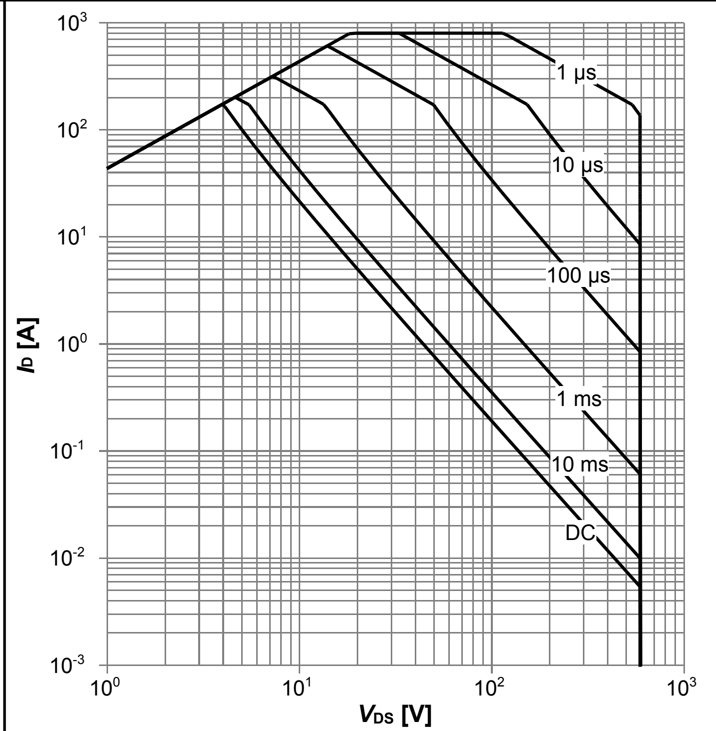
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



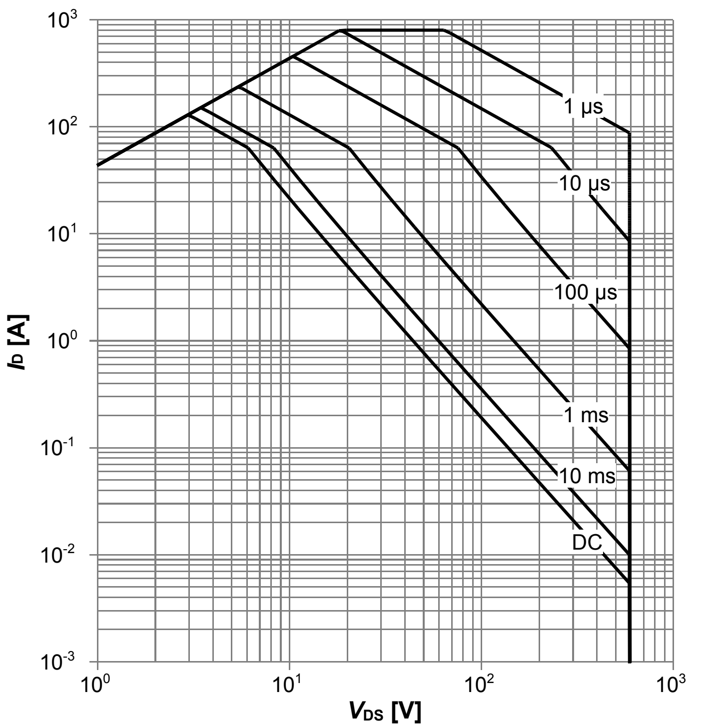
P_{tot}=f(T_C)

Diagram 2: Safe operating area



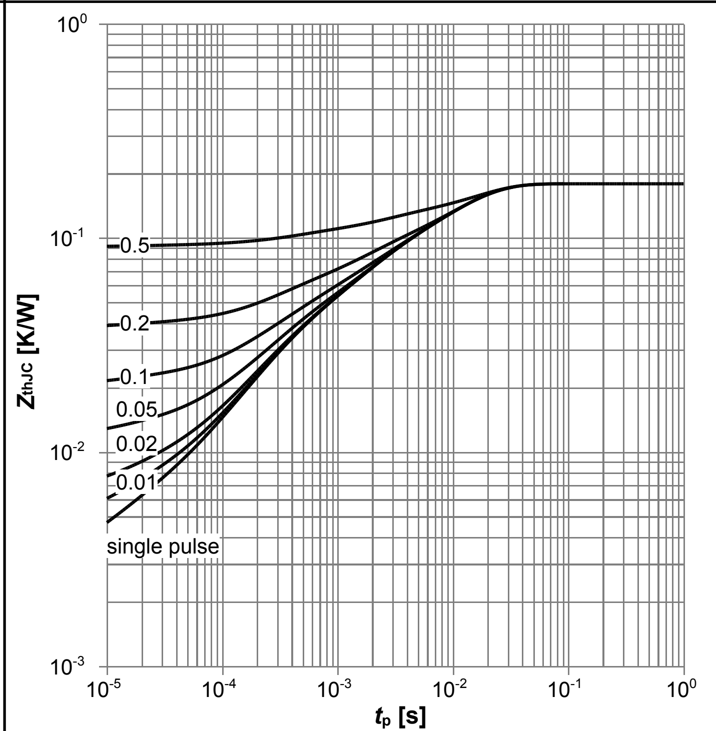
I_D=f(V_{DS}); T_C=25 °C; D=0; parameter: t_p

Diagram 3: Safe operating area



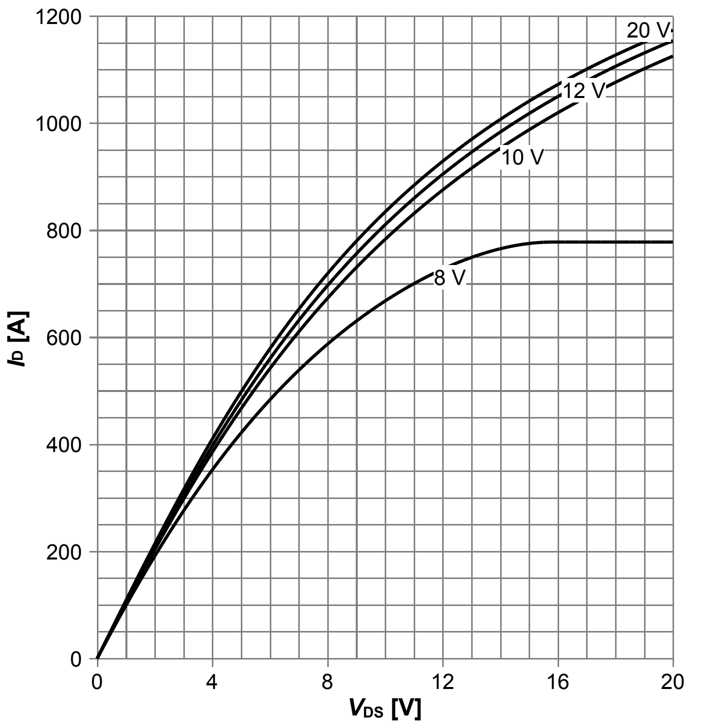
I_D=f(V_{DS}); T_C=80 °C; D=0; parameter: t_p

Diagram 4: Max. transient thermal impedance



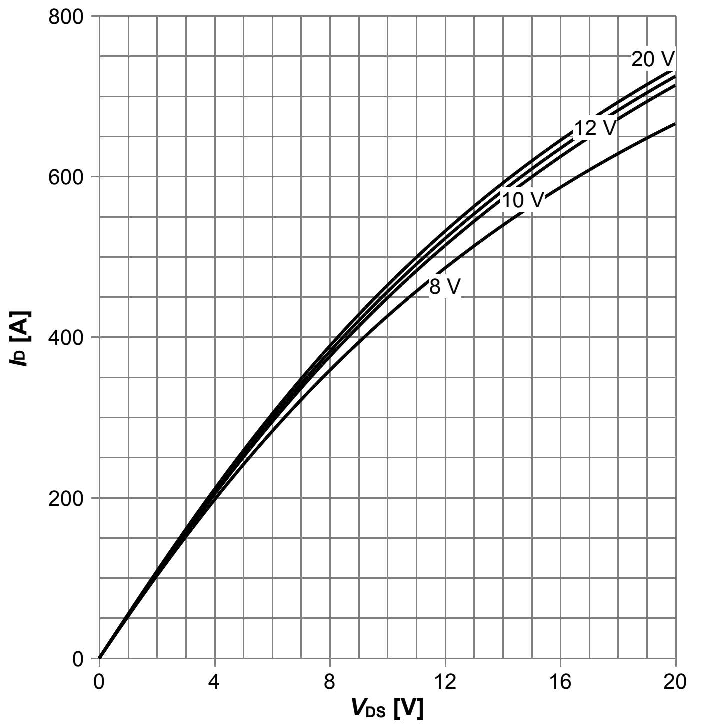
Z_{thJC} =f(t_P); parameter: D=t_p/T

Diagram 5: Typ. output characteristics



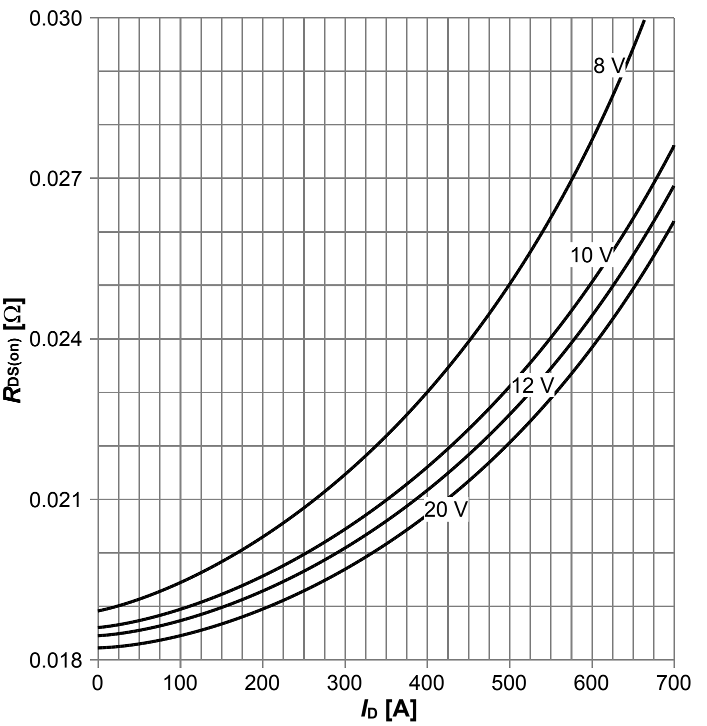
I_D=f(V_{DS}); T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. output characteristics



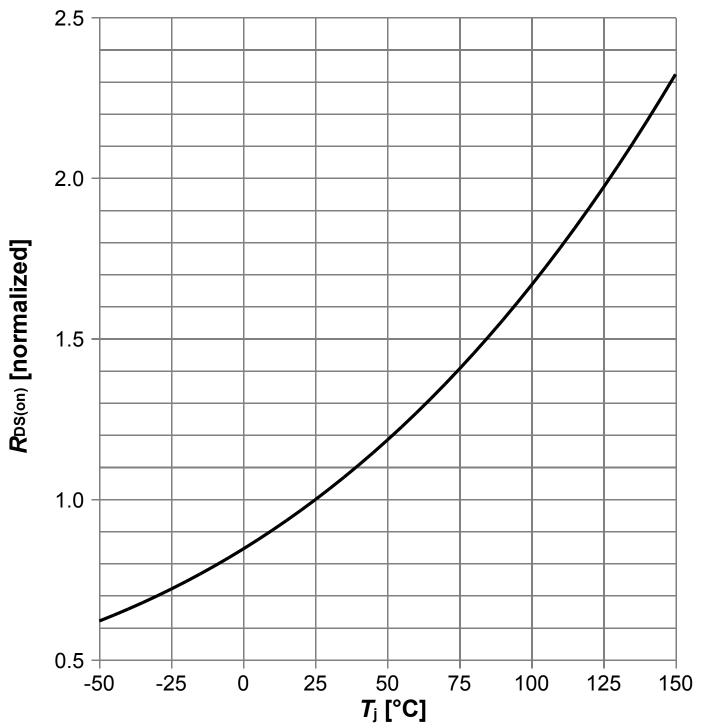
I_D=f(V_{DS}); T_j=125 °C; parameter: V_{GS}

Diagram 7: Typ. drain-source on-state resistance



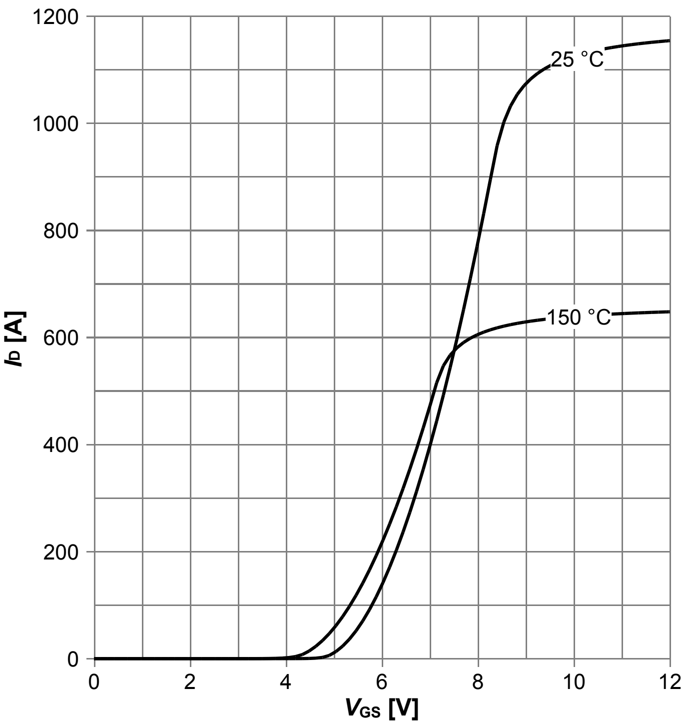
$R_{DS(on)}$=f(I_D); T_j=125 °C; parameter: V_{GS}

Diagram 8: Drain-source on-state resistance



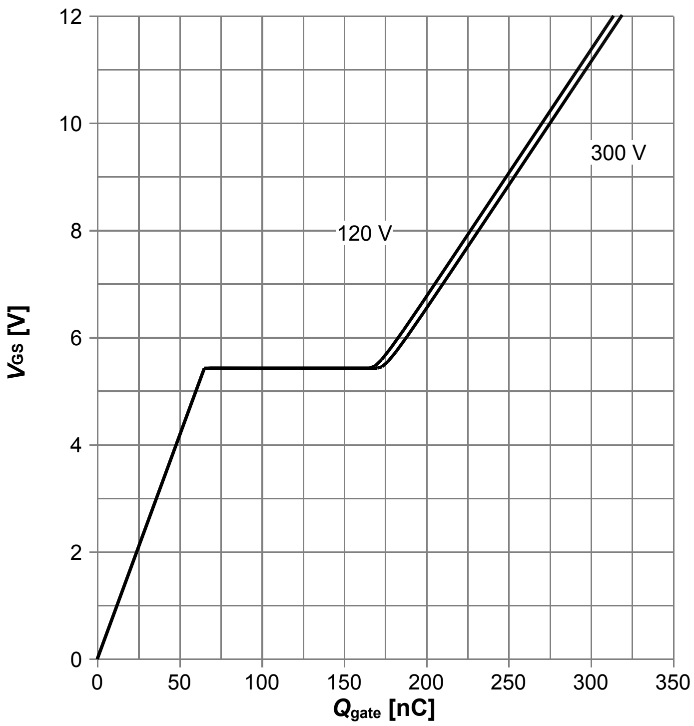
$R_{DS(on)}$=f(T_j); I_D=50 A; V_{GS}=12 V

Diagram 9: Typ. transfer characteristics



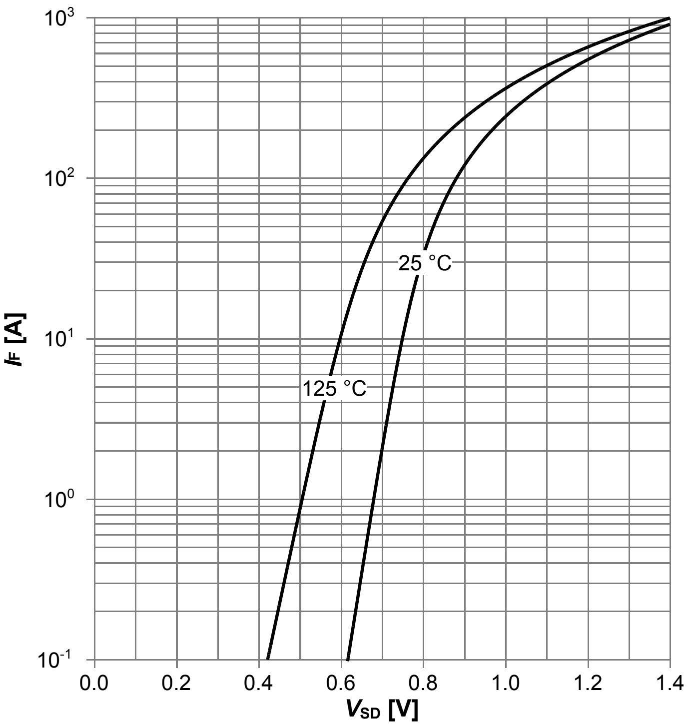
I_D=f(V_{GS}); V_{DS}=20V; parameter: T_j

Diagram 10: Typ. gate charge



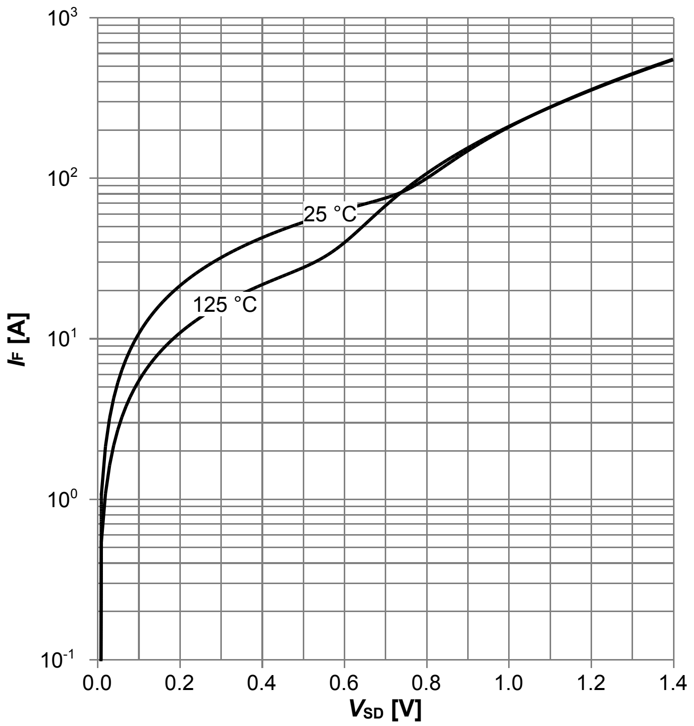
V_{GS}=f(Q_{gate}); I_D=50 A pulsed; parameter: V_{DD}

Diagram 11: Forward characteristics of reverse diode



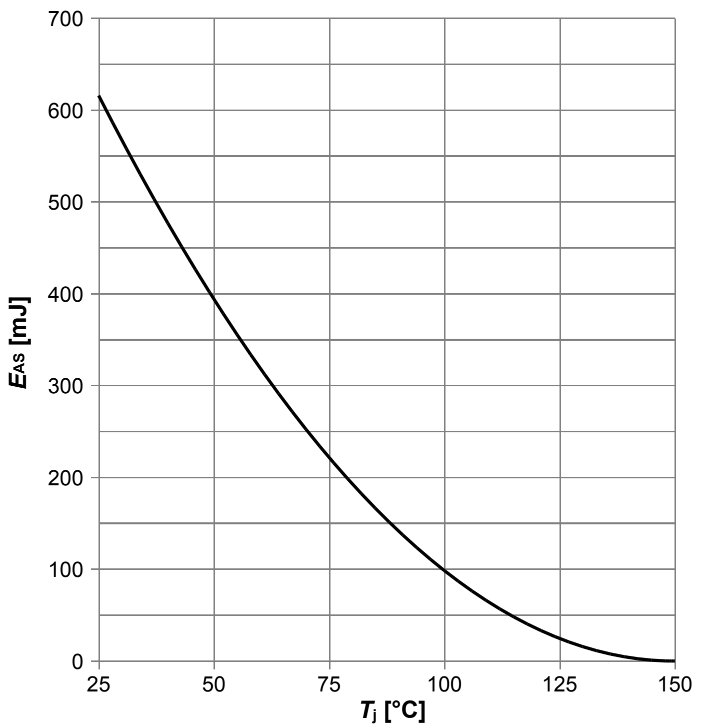
I_F=f(V_{SD}); V_{GS}=0 V; parameter: T_j

Diagram 12: Forward characteristics of reverse diode



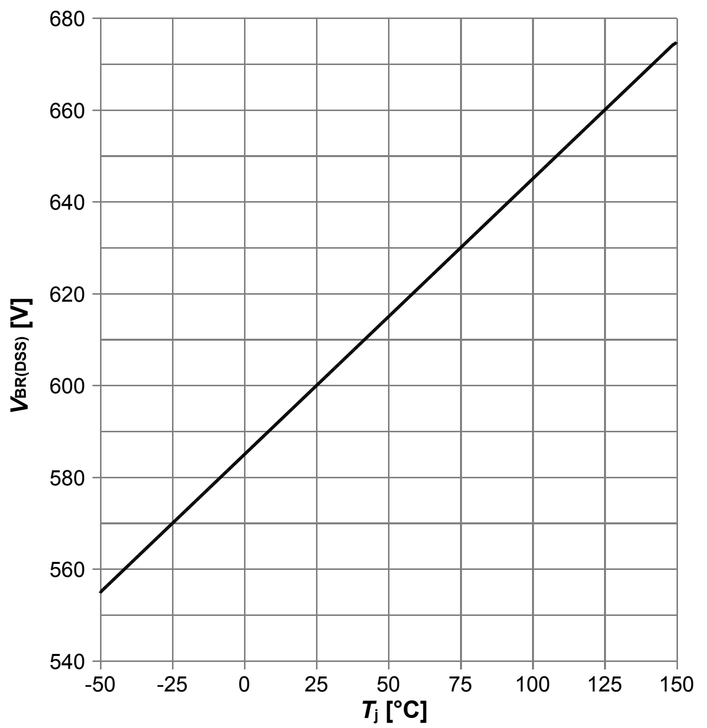
I_F=f(V_{SD}); V_{GS}=12 V; parameter: T_j

Diagram 13: Avalanche energy



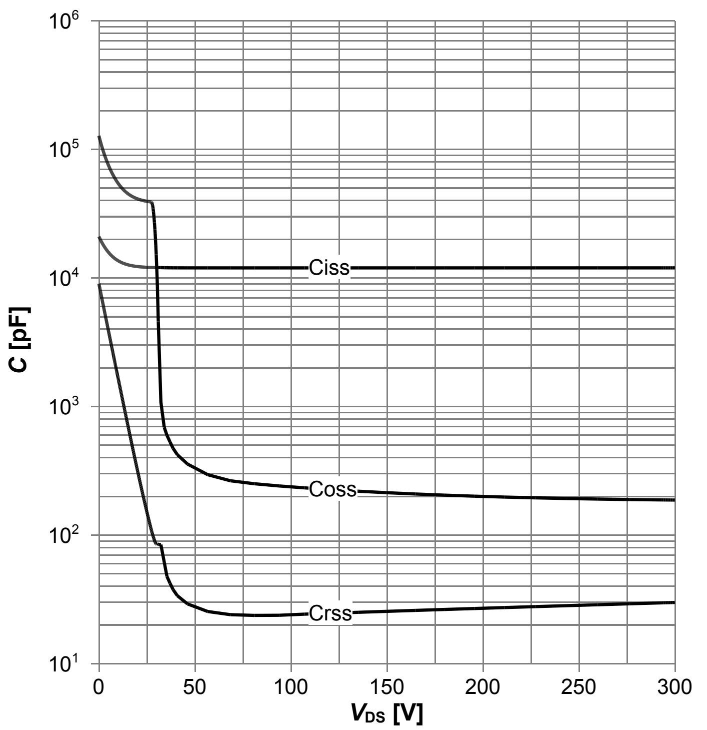
E_{AS}=f(T_j); I_D=6.3 A; V_{DD}=50 V

Diagram 14: Drain-source breakdown voltage



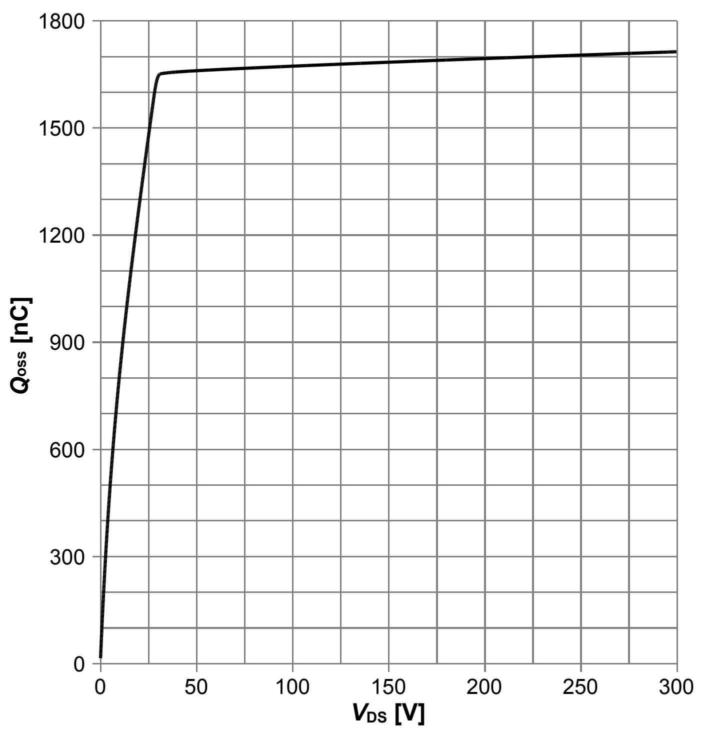
$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Diagram 15: Typ. capacitances



C=f(V_{DS}); V_{GS}=0 V; f=250 kHz

Diagram 17: Typ. Qoss output charge



Q_{oss}=f(V_{DS}); V_{GS}=0 V

5 Test Circuits

Table 8 Diode characteristics

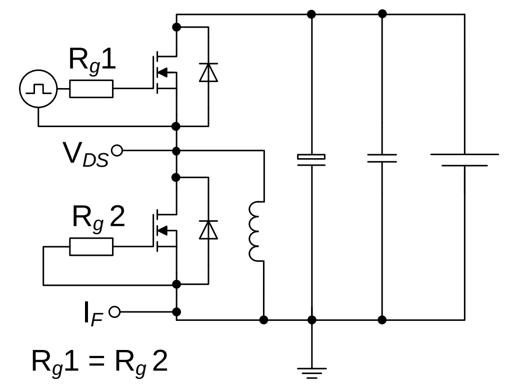
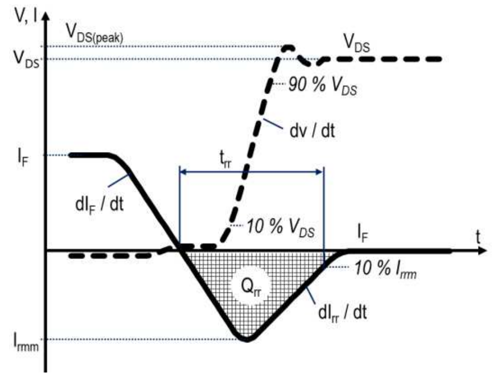
<table>
<tr><th>Test circuit for diode characteristics</th><th>Diode recovery waveform</th></tr>
<tr><td>
</td><td>
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Table 9 Switching times (ss)

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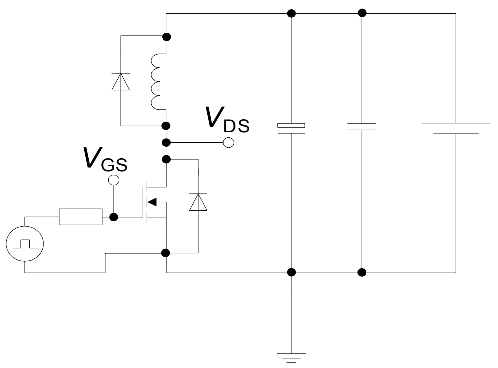
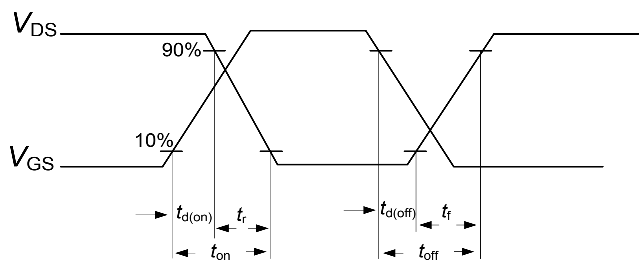
<tr><th>Switching times test circuit for inductive load</th><th>Switching times waveform</th></tr>
<tr><td>
</td><td>
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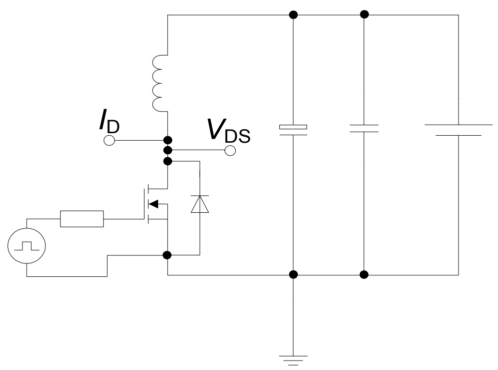
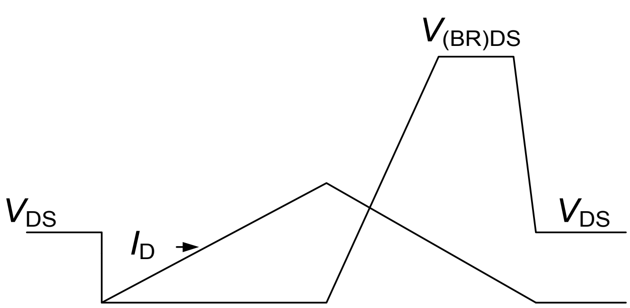
Table 10 Unclamped inductive load (ss)

<table>
<tr><th>Unclamped inductive load test circuit</th><th>Unclamped inductive waveform</th></tr>
<tr><td>
</td><td>
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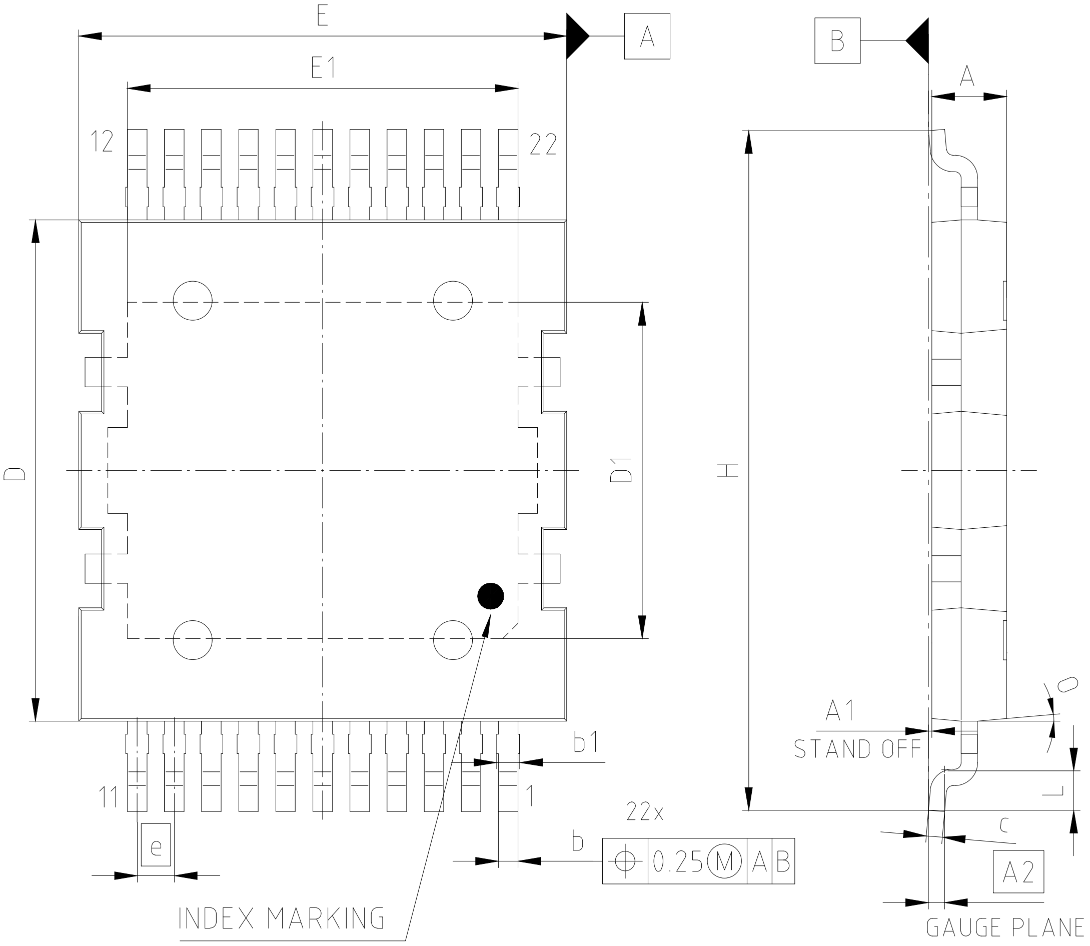
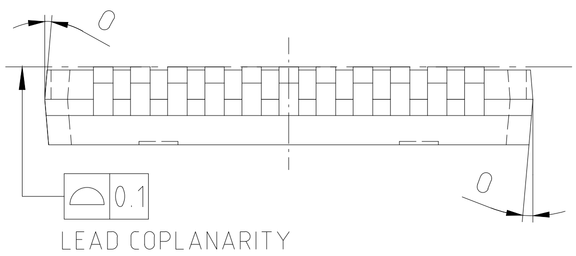
6 Package Outlines





PACKAGE - GROUP NUMBER:	PG-HDSOP-22-U02	
DIMENSIONS	**MILLIMETERS**	
	MIN.	MAX.
A	2.20	2.35
A1	0.00	0.15
A2	0.5	
b	0.50	0.70
b1	0.50	0.90
c	0.46	0.58
D	15.30	15.50
D1	10.23	10.43
E	14.90	15.10
E1	11.91	12.11
e	1.14	
N	22	
H	20.81	21.11
L	1.20	1.40
O	5°	

Figure 1 Outline PG-HDSOP-22, dimensions in mm

7 Appendix A

Table 11 Related Links

- **IFX CoolMOS S7 Webpage:** www.infineon.com
- **IFX CoolMOS S7 application note:** www.infineon.com
- **IFX CoolMOS S7 simulation model:** www.infineon.com
- **IFX Design tools:** www.infineon.com

Revision History

IPQC60R010S7

Revision: 2023-11-22, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2022-11-23	Release of final version
2.1	2023-11-06	Added footmark for pulsed drain current
2.2	2023-11-22	Additional maximum parameter for high current turn off added to datasheet for SSCB, SSR and motor start applications; Removed footmark from pulsed drain current

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